

Product Data Sheet

Industrial SD Memory Card

S-200 Series

SPI, SD compliant

BU: Flash Products





S-200 SERIES INDUSTRIAL SD MEMORY CARD

1 Feature

- Custom-designed, highly-integrated memory controller
 - Fully compliant with SD Memory Card specification 2.0
 - Four integrated 4KByte Sector Buffers for fast data transfer
 - SPI Mode support
- Standard SD Memory Card form factor
 - o 32.0mm x 24.0mm x 2.1mm
 - Write Protect slider
- 2.7...3.6V normal operating voltage
- 2.0...3.6V basic communication (CMDo, 15, 55 ACMD41) voltage
- Low-power CMOS technology
- Wear Leveling: equal wear leveling of static and dynamic data

The wear leveling assures that dynamic data as well as static data is balanced evenly across the memory. With that the maximum write endurance of the device is guaranteed.

- Patented power-off reliability
 - No data loss of older sectors
 - Max. 16 sectors data loss (old data kept) if power off during writing
- High reliability
 - Best available SLC NAND Flash technology
 - Designed for embedded market
 - o MTBF: > 3,000,000 hours
 - Number of insertions: >10,000
 - Extended Temperature range -25° up to 85°C
 - o Optional industrial Temperature range available -40° up to 85°C
- Hot swappable
- High performance
 - o SD burst up to 25MB/s
 - SD Low speed o...25MHz clock rate
 - SD High speed 25...50MHz clock rate
 - Flash burst up to 40MB/s
- Available densities
 - o up to 2GBytes (higher densities are in the SDHC S-220 Series available up to 8GB)
- Controlled BOM
- Life Time Monitoring SD/SPI with standard or vendor commands





2 Order Information

2.1 Extended and Industrial Temperature range

Table 1: Product List for standard products

Capacity	Part Number
512MB	SFSD0512LgBN1TO-t-ME-1x1-STD
1GB	SFSD1024LgBN2TO-t-ME-1x1-STD
2GB	SFSD2048LgBN2TO-t-DF-1x1-STD

g defines the product generation

t defines the temperature range (E=-25°C to +85°C, I=-40°C to +85°C)

x defines the FW

2.2 Current product list

Table 2: General Product List

Capacity	Part Number
512MB	SFSD0512L1BN1TO-E-ME-161-STD
1GB	SFSD1024L1BN2TO-E-ME-161-STD
2GB	SFSD2048L1BN2TO-E-DF-161-STD
512MB	SFSD0512L1BN1TO-I-ME-161-STD
1GB	SFSD1024L1BN2TO-I-ME-161-STD
2GB	SFSD2048L1BN2TO-I-DF-161-STD

2.3 Offered options for customer projects

- Customer specified strings and IDs (MID, OID, PNM, PRV)
- Customer specified capacities
- Preload service
- Customized labels & lasering



Contents

S-200 SERIES INDUSTRIAL SD MEMORY CARD	
1 FEATURE	
2 ORDER INFORMATION	3
2.1 Extended and Industrial Temperature range	3
3 PRODUCT SPECIFICATION	5
3.1 SYSTEM PERFORMANCE	5 5
4 CAPACITY SPECIFICATION	6
5 CARD PHYSICAL	
5.1 Physical description	
6 ELECTRICAL INTERFACE	9
6.1 ELECTRICAL DESCRIPTION	
7 HOST ACCESS SPECIFICATION	14
7.1 SD AND SPI Bus Modes	
8 CARD LIFETIME INFORMATION DATA	20
9 ROHS AND WEEE UPDATE FROM SWISSBIT	22
10 PART NUMBER DECODER	24
11 SWISSBIT LABEL SPECIFICATION	20
11.1 FRONT SIDE LABEL	
12 REVISION HISTORY	



3 Product Specification

The SD Memory Card is a small form factor non-volatile memory card which provides high capacity data storage. Its aim is to capture, retain and transport data, audio and images, facilitating the transfer of all types of digital information between a large variety of digital systems.

The Card operates in two basic modes:

- SD card mode
- SPI mode

The SD Memory Card also supports SD **High Speed mode** with up to 50MHz clock frequency.

The cards are compliant with

- SD Memory Card Specification Part 1, Physical layer Specification V2.00
- SD Memory Card Specification Part 2, File System Specification V2.00

The Card has an internal **intelligent controller** which manages interface protocols, data storage and retrieval as well as hardware RS-code **Error Correction Code (ECC)**, **defect handling**, **diagnostics and clock control**.

The wear leveling mechanism assures an equal usage of the Flash memory cells to extend the life time.

The hardware RS-code ECC allows to detect and correct 4 symbols per 528 Bytes.

The Card has a **voltage detector** and a powerful **power-loss management feature** to prevent data corruption after power-down.

The power consumption is very low.

The data retention is 10 years @ life begin.

The cards are offered in 2 temperature ranges

Extended -25°C...85°C

• Industrial -40...85°C on request

The cards are RoHS compliant and lead-free.

3.1 System Performance

Table 3: Performance

System Performance	typ	max	Unit	
Burst Data transfer Rate (max clock 50MHz)			25 (166X) ⁽¹⁾	
Custained Cognential Dead	512MB	18.4 (1)(2)	21	
Sustained Sequential Read	1GB - 2GB	18.4 (1)(2)	21	MB/s
Sustained Cognential Write	512MB	6.6 (1)(2)	13	
Sustained Sequential Write	1GB - 2GB	12.8 (1)(2)	18	

- 1. All values refer to Toshiba Flash 4Gb SD Memory Card in 4bit SD mode 50MHz, cycle time 20ns, write/read file sequential.
- 2. Sustained Speed measured with SanDisk Mobile mate USB-SD Memory Card reader. It depends on burst speed, flash type and number, and file size

3.2 Environmental Specifications

3.2.1 Recommended Operating Conditions

Table 4: SD Memory Card Recommended Operating Conditions

Parameter	min	typ	max	Unit
Commercial Operating Temperature	0	25	70	°C
Industrial Operating Temperature	-40	25	85	°C
Power Supply VCC (3.3V)	2.7	3.3	3.6	V

Table 5: Current consumption

Current Consumption (type)	typ	max	Unit
Read	28	40	
Write	55	60	mΛ
Sleep Mode	0.2	0.3	mA

3.2.2 Recommended Storage Conditions

Table 6: SD Memory Card Recommended Storage Conditions

Parameter	min	typ	max	Unit
Commercial Storage Temperature	-40	25	85	°C
Industrial storage Temperature	-40	25	100	°C



3.2.3 Humidity & ESD

Table 7: Humidity & ESD

Parameter	Operating	Non Operating	
Humidity (non-condensing)	max 95%		
ESD according to IEC61000-4-2	Non Contact Pads area:	Contact Pads:	
Human body model	±8 kV (coupling plane	±4 kV, Human body model	
±4 kV 100 pf/1.5 k0hm	discharge)	according to IEC61000-4-2	
Machine model	±15 kV (air discharge)		
±0.25 kV 200 pf/o 0hm	Human body model according		
	to IEC61000-4-2		

3.2.4 Durability

Table 8: Durability

Parameter	Operating	Non Operating		
Salt water spray	3% NaCl/35°C; 24h ac	3% NaCl/35°C; 24h acc. MIL STD Method 1009		
Solar Exposure	1000W/m2 @ 400°C			
Impermeability	I	P67		
UV Light Exposure	UV: 254nr	n, 15Ws/cm2		
Insertions	>10	0,000		
Drop test	1.5m	1.5m free fall		
Bending	10N			
Torque	0.15Nm or ±2.5deg			
Bump	25g; 6ms; ±3	x 4000 shocks		
Shock	1000	1000 g max.		
Vibration (peak -to-peak)	15G	max.		
Minimum moving force of WP slider	0	.4N		

3.3 Physical Dimensions

Table 9: Physical Dimensions

Physical Dimensions	Value	Unit
Length	32.00±0.10	
Width	24.00±0.10	mm
Thickness	2.10±0.15	
Weight (typ.)	2	g

3.4 Reliability

Table 10: Reliability

Parameter	Value
Data Retention	10 years (JEDEC47G)

4 Capacity specification

Table 11: SD Memory Card capacity specification

.as.a ssas., aa.a capacity speciments				
Capacity	Sectors_card	Total addressable capacity (Byte)		
512MB	998,912	511,442,944		
1GB	2,001,920	1,024,983,040		
2GB	4,016,128	2,056,257,536		

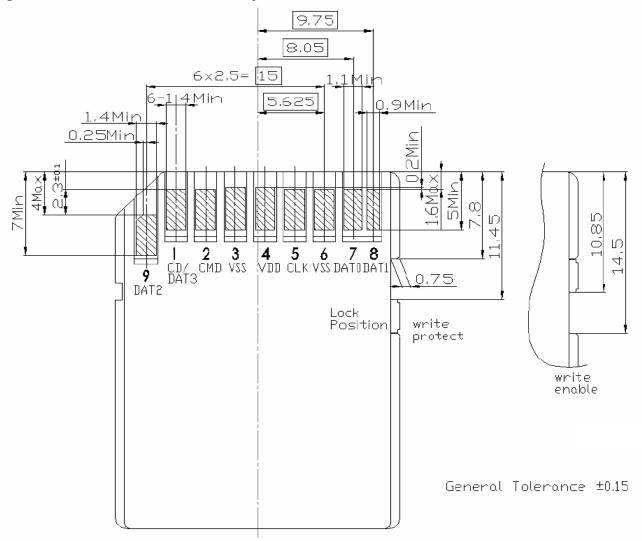


5 Card physical

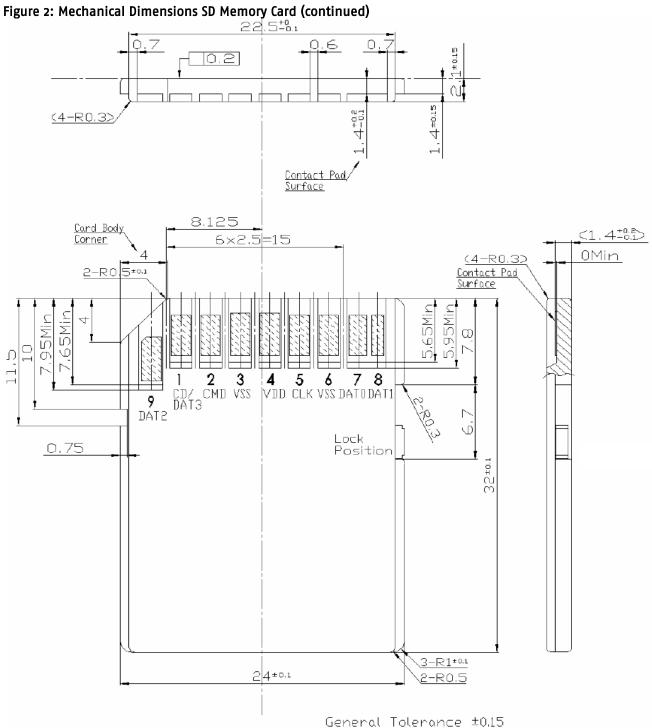
5.1 Physical description

The SD Memory Card contains a single chip controller and Flash memory module(s). The controller interfaces with a host system allowing data to be written to and read from the Flash memory module(s). Figure 1 and Figure 2 show card dimensions.

Figure 1: Mechanical Dimensions SD Memory Card









6 Electrical interface

6.1 Electrical description

Figure 3: SD Memory Card Block Diagram

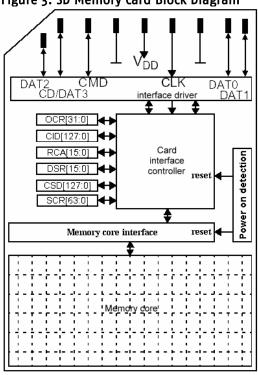


Figure 4: SD Memory Card Shape and Interface (Top View)

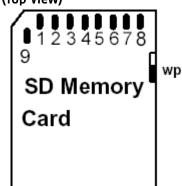


Table 12: SD Memory Card Pad Assignment

Pin #			SD Mode	SPI Mode			
	Name	Type ¹	Description	Name	Type ¹	Description	
1	CD/DAT3 ²	I/O/PP3	Card Detect/ Data Line [Bit 3]	CS	3	Chip Select (neg true)	
2	CMD	PP	Command/Response	DI	I	Data In	
3	VSS1	S	Supply voltage ground	VSS	S	Supply voltage ground	
4	VDD	S	Supply voltage	VDD	S	Supply voltage	
5	CLK	I	Clock	SCLK	I	Clock	
6	VSS2		Supply voltage ground	VSS2	S	Supply voltage ground	
7	DATo	I/O/PP	Data Line [Bit o]	DO	O/PP	Data Out	
8	DAT1 ⁴	1/0/PP	Data Line [Bit 1]	RSV			
9	DAT2 ⁵	1/0/PP	Data Line [Bit 2]	RSV			

Notes:

- 1) S: power supply; I: input; O: output using push-pull drivers; PP: I/O using push-pull drivers
- 2) The extended DAT lines (DAT1-DAT3) are input on power up. They start to operate as DAT lines after SET_BUS_WIDTH command. The Host shall keep its own DAT1-DAT3 lines in input mode, as well, while they are not used.
- 3) At power up this line has a 50k0hm pull up enabled in the card. This resistor serves two functions Card detection and Mode Selection. For Mode Selection, the host can drive the line high or let it be pulled high to select SD mode. If the host wants to select SPI mode it should drive the line low. For Card detection, the host detects that the line is pulled high. This pull-up should be disconnected by the user, during regular data transfer, with SET_CLR_CARD_DETECT (ACMD42) command
- 4) DAT1 line may be used as Interrupt Output (from the Card) in SDIO mode during all the times that it is not in use for data transfer operations (refer to "SDIO Card Specification" for further details).
- 5) DAT2 line may be used as Read Wait signal in SDIO mode (refer to "SDIO Card Specification" for further details).



6.2 DC characteristics

Measurements are at Recommended Operating Conditions unless otherwise specified.

Table 13: DC Characteristics

Symbol	Parameter	Min	Тур	Max	Unit	Notes
	Peak Voltage on all Lines	-0.3		V _{DD} +0.3	V	
V _{OH}	Output HIGH Voltage	0.75*V _{DD}			V	at -2mA
V_{OL}	Output LOW Voltage			0.125*V _{DD}	٧	at 2mA
V_{IH}	Input HIGH Voltage	0.625*V _{DD}		V _{DD} +0.3	٧	
V_{IL}	Input LOW Voltage	-0.3		0.25*V _{DD}	V	
	Operating Current		35	50	mA	
I _{DD}	Pre-initialization Standby Current			3	mA	
	Post-initialization Standby Current		100	200	μΑ	
I _{II}	Input Leakage Current	-10		10	μΑ	without
I _{LO}	Output Leakage Current	-10		10	μΑ	pull up R

Figure 5: Bus Signal levels

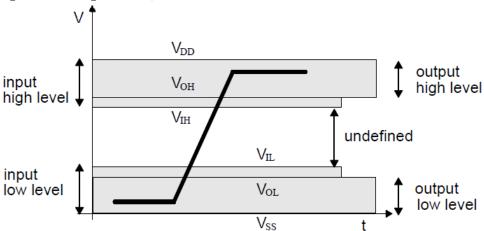


Table 14: SD Memory Card Recommended Operating Conditions

Symbol	-	min	typ	max	unit	
		Normal Operating Status	2.7	3.3	3.6	V
V _{DD}	Supply Voltage	Basic Communication (CMDo, CMD15, CMD55, ACMD41)	2.0	3.3	3.6	V
_	Power Up Time (from oV to VDD min)			250	ms



6.3 Signal Loading

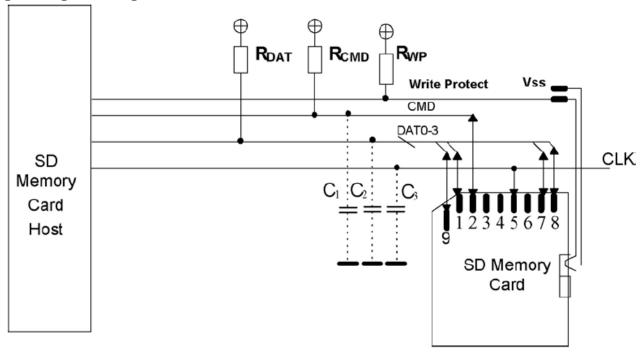
The total capacitance C_L is the sum of the bus master capacitance C_{HOST} , the bus capacitance C_{BUS} , and the capacitance C_{CARD} of the card connected to the line:

 $C_L = C_{HOST} + C_{BUS} + C_{CARD}$ To allow the sum of the host and bus capacitances to be up to 20pF for the card, the following conditions in the table below are met by the card.

Table 15: Signal loading

Parameter	Symbol	Min	Max	Unit	Notes
Pull up resistance	R_{CMD} , R_{DAT}	10	100	k0hm	To prevent bus floating
Pull up resistance inside card (pin1)	R_{DAT_3}	10	90	k0hm	May be used for card detection
Bus signal line capacitance for each signal line	C^{Γ}		40	pF	Single card C _{HOST} +C _{BUS} shall not exceed 30pF
Signal card capacitance for each signal pin	C_{CARD}		10	pF	Single card
Signal line inductance			16	nH	$f \le 20MHz$
Capacioty Connected to Power line	C _C		5µF	μF	To prevent inrush current

Figure 6: Signal Loading





6.4 AC characteristics

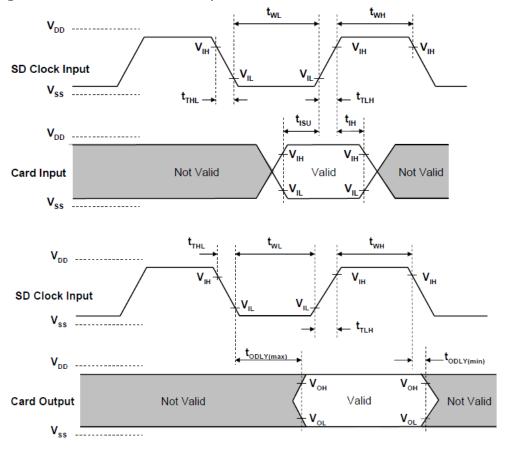
6.4.1 Default Speed mode (0 - 25MHz)

Table 16: AC Characteristics Default Speed Mode

Parameter	Symbol	Min	Max	Unit	Notes
Clock Clk All values are referred to min	(VIH) and	max (VIL)			
Clock frequency in data transfer mode	f_{pp}	0	25	MHz	
Clock frequency in card id mode	$f_{\mathtt{OD}}$	0/100 1)	400	kHz	
Clock low time	t_{WL}	10		ns	C _{card} ≤1opF (1 card)
Clock high time	t_{WH}	10		ns	C _{CARD} \(\text{IOpt (i cald)}
Clock rise time	$t_{\scriptscriptstyleTLH}$		10	ns	
Clock fall time	$t_{\scriptscriptstyleTHL}$		10	ns	
Inputs CMD, DAT (referenced to CLK)					
CMD, DAT input setup time	t_{ISU}	5		ns	C _{card} ≤1opF (1 card)
CMD, DAT input hold time	t_{IH}	5		ns	C _{CARD} ~ 10 pt (1 card)
Outputs CMD, DAT (referenced to CLK)					
CMD, DAT output delay time during Data	+	0	11.	ns	
Transfer Mode	t _{odly}	0	14	115	$C_1 \leq 4opF$ (1 card)
CMD, DAT output delay time during Identification Mode	t _{odly}	0	50	ns	վ <u>-</u> 40pi (i caiu)

Notes

Figure 7: AC Characteristics Default Speed Mode



^{1.} o kHz means to stop the clock. The minimum clock frequency should not be below 100kHz



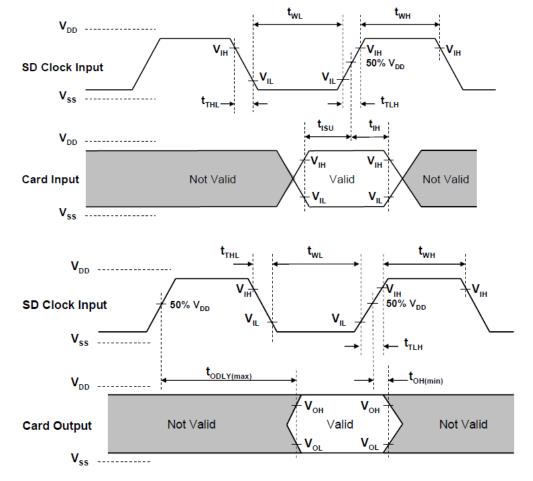
6.4.2 High Speed mode (0 - 50MHz)

Table 17: AC Characteristics High Speed Mode

Parameter	Symbol	Min	Max	Unit	Notes			
Clock Clk All values are referred to min (VIH) and max (VIL)								
Clock frequency in data transfer mode	f_{pp}	0	50	MHz				
Clock low time	t_{WL}	7		ns				
Clock high time	t_{w_H}	7		ns	C _{card} ≤1opF (1 card)			
Clock rise time	$t_{\scriptscriptstyleTLH}$		3	ns				
Clock fall time	$t_{\scriptscriptstyleTHL}$		3	ns				
Inputs CMD, DAT (referenced to CLK)								
input setup time	t _{ISU}	6		ns	C _{CARD} ≤1opF (1 card)			
input hold time	t _{IH}	2		ns	C _{CARD} > 10pt (1 card)			
Outputs CMD, DAT (referenced to CLK)	Outputs CMD, DAT (referenced to CLK)							
output delay time during data transfer mode	todly		14	ns	C _L ≤4opF (1 card)			
output hold time	t _{oh}	2.5		ns	$C_{L} \ge 15 pF$ (1 card)			

Notes

Figure 8: AC Characteristics High Speed Mode



^{1.} In order to satisfy severe timing, the host shall drive only one card with max 4opF total at each line.



7 Host access Specification

The following chapters summarize how the host accesses the card:

- Chapter 7.1 summarizes the SD and SPI buses.
- Chapter 7.2 summarizes the registers.

7.1 SD and SPI Bus Modes

The card supports SD and the SPI Bus modes. Application can chose either one of the modes. Mode selection is transparent to the host. The card automatically detects the mode of the reset command and will expect all further communication to be in the same communication mode. The SD mode uses a 4-bit high performance data transfer, and the SPI mode provides compatible interface to MMC host systems with little redesign, but with a lower performance.

7.1.1 SD Bus Mode Protocol

The SD Bus mode has a single master (host) and multiple slaves (cards) synchronous topology. Clock, power, and ground signals are common to all cards. After power up, the SD Bus mode uses DATo only; after initialization, the host can change the cards' bus width from 1 bit (DATo) to 4 bits (DATo-DAT3). In high speed mode, only one card can be connected to the bus.

Communication over the SD bus is based on command and data bit streams which are initiated by a start bit and terminated by a stop bit.

- Command: a command is a token which starts an operation. A command is sent from the host either to a single card (addressed command) or to all connected cards (broadcast command). A command is transferred serially on the CMD line.
- Response: a response is a token which is sent from an addressed card, or (synchronously) from all
 connected cards, to the host as an answer to a previously received command. A response is transferred
 serially on the CMD line.
- Data: data can be transferred from the card to the host or vice versa. Data is transferred via the data lines.

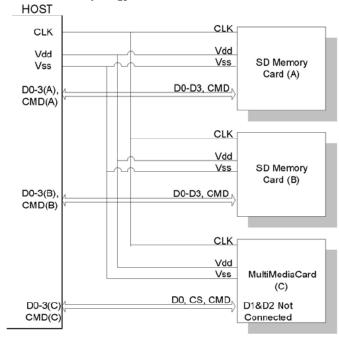
The SD bus signals are listed in Table 18, and the SD bus topology is illustrated in Figure 9: SD Bus Topology.

Table 18: SD Bus Signals

Signal	Description			
CLK	Host to card clock signal			
CMD	Bidirectional Command/Response signal			
DATo-DAT3	4 Bidirectional data signals			
Vdd, Vss	Power and Ground			



Figure 9: SD Bus Topology



7.1.2 SPI Bus Mode Protocol

The Serial Parallel Interface (SPI) Bus is a general purpose synchronous serial interface. The SPI mode consists of a secondary communication protocol. The interface is selected during the first reset command after power up (CMDo) and it cannot be changed once the card is powered on.

While the SD channel is based on command and data bit streams which are initiated by a start bit and terminated by a stop bit, the SPI channel is byte oriented. Every command or data block is built of 8-bit bytes and is byte aligned to the CS signal.

The card identification and addressing methods are replaced by a hardware Chip Select (CS) signal. There are no broadcast commands. For every command, a card (slave) is selected by asserting (active low) the CS signal. The CS signal must be continuously active for the duration of the SPI transaction (command, response and data). The only exception occurs during card programming, when the host can de-assert the CS signal without affecting the programming process.

The bidirectional CMD and DAT lines are replaced by unidirectional dataIn and dataOut signals.

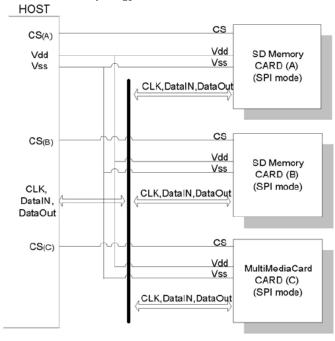
The SPI bus signals are listed Table 19 and the SPI bus topology is illustrated in Figure 10.

Table 19: SPI Bus Signals

Signal	Description
/CS	Host to card chip select
CLK	Host to card clock signal
Data In	Host to card data signal
Data Out	Card to host data signal
Vdd, Vss	Power and ground



Figure 10: SPI bus topology



7.1.3 Mode Selection

The SD Memory Card wakes up in the SD mode. It will enter SPI mode if the CS signal is asserted (negative) during the reception of the reset command (CMDo) and the card is in idle state. If the card recognizes that the SD mode is required it will not respond to the command and remain in the SD mode.

If SPI mode is required the card will switch to SPI and respond with the SPI mode R1 response.

The only way to return to the SD mode is by entering the power cycle. In SPI mode the SD Memory Card protocol state machine is not observed. All the SD Memory Card commands supported in SPI mode are always available. During the initialization sequence, if the host gets Illegal Command indication for ACMD41 sent to the card, it may assume that the card is MultiMediaCard. In that case it should re-start the card as MultiMediaCard using CMDo and CMD1.

7.2 Card Registers

The SD Memory Card has five registers. Refer to Table 20 to Table 25 for detail.

Table 20. SD Memory Card registers

		nory card registers	
Register Name		Description	Function
CID	178		This register contains the card identification information used during the Card Identification phase.
OCR			This register describes the operating voltage range and contains the status bit in the power supply.
CSD			This register provides information on how to access the card content. Some fields of this register are writeable by PROGRAM_CSD (CMD27).
SCR		SD Memory Card's Special features	This register provides information on special features.
RCA	16	Relative Card Address	This register carries the card address is SD Memory Card mode.

Table 21: CID register

Swissbit AG

Switzerland

Register Name	Bit Width	Description	typ. value
MID	8	Manufacture ID	ox5d
OID	16	OEM/Application ID	0X5342
PNM	PNM 40		"LxBNc"
			c=number of channels
PRV 8		Product Version	0X04



			can change
PSN	32	Product Serial Number	XXXXXXXX
_	4	Reserved	0X0
MDT	12	Manufacture Date	oxyym
CRC	7	Check sum of CID contents	chksm
_	1	Not used; always=1	1

Table 22: OCR register

OCR bit position	VDD voltage window	typ. value	OCR bit position	VDD voltage window	typ. value
0-3	Reserved	0	15	2.7-2.8	1
4	1.6-1.7	0	16	2.8-2.9	1
5	1.7-1.8	0	17	2.9-3.0	1
6	1.8-1.9	0	18	3.0-3.1	1
7	1.9-2.0	0	19	3.1-3.2	1
8	2.0-2.1	0	20	3.2-3.3	1
9	2.1-2.2	0	21	3.3-3.4	1
10	2.2-2.3	0	22	3.4-3.5	1
11	2.3-2.4	0	23	3.5-3.6	1
12	2.4-2.5	0	24-30	Reserved	
13	2.5-2.6	0	30	Card Capacity Status (CCS)	*1)
14	2.6-2.7	0	31	o=busy; 1=ready	*2)

Notes

- 1. This bit is valid only when the card power up status bit is set.
- 2. This bit is set to LOW if the card has not finished the power up routine.



Table 23: CSD register

125 6 Reserved	Register Name	First Bit	Bit Width	Description	typ. Value
NACC	CSD_STRUCTURE	127	2	CSD structure	00
NSAC		125	6	Reserved	000000
RRAN_SPEED 103 8	TAAC	119	8		00001110
CCC 95 12 Card command classes 010110110101 READ_BL_LEN 83 4 Read data block length 1001 READ_BL_PARTIAL 79 1 Partial blocks for read allowed 1 WRITE_BLK_MISALIGN 78 1 Write block misalignment 0 OBSR_IMP 76 1 DSR implemented 0 OSSR_IMP 76 1 DSR implemented 0 C_SIZE 73 12 Device size xxxx**) VDD_R_CURR_MIN 61 3 VDD min read current 110 VDD_R_CURR_MAX 58 3 VDD max read current 110 VDD_W_CURR_MAX 58 3 VDD max read current 110 VDD_W_CURR_MAX 52 3 VDD max write current 110 VDD_W_CURR_MAX 52 3 VDD max write current 110 C_SIZE_MULT 49 3 Device size multiplier 110**) ERASE_BLK_EN 46 1 Erase sector size 1	NSAC	111	8	Data read access time 2 (CLK cycle)	0000000
READ_BL_EN 83 4 Read data block length 1001 READ_BL_PARTIAL 79 1 Partial blocks for read allowed 1 MRITE_BLK_MISALIGN 78 1 Write block misalignment 0 OBSR_IMP 76 1 DSR implemented 0 OBSR_IMP 76 1 DSR implemented 0 CSIZE 73 12 Device Size xxx**) VDD R_CURR_MIN 61 3 VDD min read current 110 VDD R_CURR_MAX 58 3 VDD min read current 110 VDD W_CURR_MIN 55 3 VDD min write current 110 VDD W_CURR_MAX 52 3 VDD max write current 110 VDD W_CURR_MAX 52 3 VDD max write current 110 SECTIZE_MULT 49 3 Device size multiplier 110**) SECTOR_SIZE 45 7 Erase sector size 1111111 WP_GRP_SIZE 38 7 Write protect group enable	TRAN_SPEED	103	8	Data transfer rate	00110010
Partial blocks for read allowed 1	CCC	95	12	Card command classes	010110110101
WRITE_BLK_MISALIGN 78	READ_BL_LEN	83	4	Read data block length	1001
READ_BLK_MISALIGN 77 1 Read block misalignment 0 DSR_IMP 76 1 DSR implemented 0 - 75 2 Reserved 00 C_SIZE 73 12 Device size xxx**) VDD_R_CURR_MIN 61 3 VDD min read current 110 VDD_R_CURR_MAX 58 3 VDD max read current 110 VDD_W_CURR_MIN 55 3 VDD min write current 110 VDD_W_CURR_MAX 52 3 VDD max write current 110 VDD_W_CURR_MAX 52 3 VDD max write current 110 C_SIZE_MULT 49 3 Device size multiplier 110*) SECTOR_SIZE 45 7 Erase sector size 1111111 WP_GRP_SIZE 38 7 Write protect group size 0000001*) WP_GRP_ENABLE 31 1 Write protect group enable 0 - 30 2 Reserved 00	READ_BL_PARTIAL	79	1	Partial blocks for read allowed	1
DSR_IMP 76 1 DSR implemented 0 C_SIZE 75 2 Reserved 00 C_SIZE 73 12 Device size xxx**) VDD_R_CURR_MIN 61 3 VDD min read current 110 VDD_W_CURR_MAX 58 3 VDD max read current 110 VDD_W_CURR_MIN 55 3 VDD min write current 110 VDD_W_CURR_MAX 52 3 VDD max write current 110 C_SIZE_MULT 49 3 Device size multiplier 110*) C_SIZE_BLK_EN 46 1 Erase single block enable 1 SECTOR_SIZE 45 7 Erase sector size 111111 NP_GRP_SIZE 38 7 Write protect group enable 0	WRITE_BLK_MISALIGN	78	1	Write block misalignment	0
75	READ_BLK_MISALIGN	77	1	Read block misalignment	0
C_SIZE	DSR_IMP	76	1	DSR implemented	0
VDD_R_CURR_MIN 61 3 VDD min read current 110 VDD_R_CURR_MAX 58 3 VDD max read current 110 VDD_W_CURR_MIN 55 3 VDD min write current 110 VDD_W_CURR_MAX 52 3 VDD max write current 110 VDD_W_CURR_MAX 52 3 VDD max write current 110 C_SIZE_MULT 49 3 Device size multiplier 110*) C_SIZE_MULT 49 3 Device size multiplier 110*) SECTOR_SIZE 45 7 Erase single block enable 1 SECTOR_SIZE 45 7 Erase sector size 1111111 NP_GRP_SIZE 38 7 Write protect group size 0000001*) NP_GRP_SIZE 38 7 Write protect group enable 0 O- 30 2 Reserved 00 REZECTOR 28 3 Write protect group enable 0 O- 28 3 Write speed factor 100 <td>_</td> <td>75</td> <td>2</td> <td>Reserved</td> <td></td>	_	75	2	Reserved	
VDD_R_CURR_MAX583VDD max read current110VDD_W_CURR_MIN553VDD min write current110VDD_W_CURR_MAX523VDD max write current110C_SIZE_MULT493Device size multiplier110*)ERASE_BLK_EN461Erase single block enable1SECTOR_SIZE457Erase sector size1111111NP_GRP_SIZE387Write protect group size0000001*)NP_GRP_ENABLE311Write protect group enable0-302Reserved00R2W_FACTOR283Write speed factor100NRITE_BL_LEN254Write data block length1001*)NRITE_BL_PARTIAL211Partial blocks for write allowed0-205Reserved000000FILE_FORMAT_GRP151File format group0 W(1)COPY141Copy flag0 W(1)DERM_WRITE_PROTECT131Permanent write protection0 W(1)TMP_WRITE_PROTECT121Temporary write protection0 W(1)TMP_WRITE_PROTECT	C_SIZE	73	12	Device size	xxx*)
VDD_W_CURR_MIN553VDD min write current110VDD_W_CURR_MAX523VDD max write current110C_SIZE_MULT493Device size multiplier110*)ERASE_BLK_EN461Erase single block enable1SECTOR_SIZE457Erase sector size1111111NP_GRP_SIZE387Write protect group size00000001*)NP_GRP_ENABLE311Write protect group enable0-302Reserved00R2W_FACTOR283Write speed factor100NRITE_BL_EN254Write data block length1001*)NRITE_BL_PARTIAL211Partial blocks for write allowed0-205Reserved000000FILE_FORMAT_GRP151File format group0 W(1)COPY141Copy flag0 W(1)DERM_WRITE_PROTECT131Permanent write protection0 W(1)IMP_WRITE_PROTECT121Temporary write protection0 W(1)IMP_WRITE_PROT	VDD_R_CURR_MIN	61	3	VDD min read current	110
VDD_W_CURR_MAX523VDD max write current110C_SIZE_MULT493Device size multiplier110*)ERASE_BLK_EN461Erase single block enable1SECTOR_SIZE457Erase sector size1111111NP_GRP_SIZE387Write protect group size00000001*)NP_GRP_ENABLE311Write protect group enable00-302Reserved00R2W_FACTOR283Write speed factor100NRITE_BL_LEN254Write data block length1001*)NRITE_BL_PARTIAL211Partial blocks for write allowed00-205Reserved00000FILE_FORMAT_GRP151File format group0 W(1)COPY141Copy flag0 W(1)PERM_WRITE_PROTECT131Permanent write protection0 W(1)TMP_WRITE_PROTECT121Temporary write protection0 W(1)TMP_WRITE_PROTECT121Temporary write protection0 W(1)THE_FORMAT112File format00 W(1)0-92Reserved00 WCRC77Checksum of CSD contentsxxxxxxxxx	VDD_R_CURR_MAX	58	3	VDD max read current	110
C_SIZE_MULT 49 3 Device size multiplier 110*) ERASE_BLK_EN 46 1 Erase single block enable 1 SECTOR_SIZE 45 7 Erase sector size 1111111 MP_GRP_SIZE 38 7 Write protect group size 00000001*) MP_GRP_ENABLE 31 1 Write protect group enable 0 GREW_FACTOR 28 3 Write speed factor 100 MRITE_BL_LEN 25 4 Write data block length 1001*) MRITE_BL_PARTIAL 21 1 Partial blocks for write allowed 0 GOP 20 5 Reserved 00000 FILE_FORMAT_GRP 15 1 File format group 0 W(1) COPY 14 1 Copy flag 0 W(1) PERM_WRITE_PROTECT 13 1 Permanent write protection 0 W(1) FILE_FORMAT 11 2 File format 00 W(1) GCRC 7 7 Checksum of CSD contents	VDD_W_CURR_MIN	55	3	VDD min write current	110
ERASE BLK_EN 46 1 Erase single block enable 1 SECTOR_SIZE 45 7 Erase sector size 1111111 NP_GRP_SIZE 38 7 Write protect group size 0000001*) NP_GRP_ENABLE 31 1 Write protect group enable 0 R2W_FACTOR 28 3 Write speed factor 100 NRITE_BL_LEN 25 4 Write data block length 1001*) NRITE_BL_PARTIAL 21 1 Partial blocks for write allowed 0 Reserved 000000 FILE_FORMAT_GRP 15 1 File format group 0 W(1) COPY 14 1 Copy flag 0 W(1) PERM_WRITE_PROTECT 13 1 Permanent write protection 0 W(1) TMP_WRITE_PROTECT 12 1 Temporary write protection 0 W(1) TMP_WRITE_PROTECT 12 1 Temporary write protection 0 W(1) FILE_FORMAT 11 2 File format 00 W(1) PERM_CRC 7 7 Checksum of CSD contents xxxxxxxx W	VDD_W_CURR_MAX	52	3	VDD max write current	110
SECTOR_SIZE 45 7 Erase sector size 1111111 NP_GRP_SIZE 38 7 Write protect group size 0000001*) NP_GRP_ENABLE 31 1 Write protect group enable 0 R2W_FACTOR 28 3 Write speed factor 100 NRITE_BL_LEN 25 4 Write data block length 1001*) NRITE_BL_PARTIAL 21 1 Partial blocks for write allowed 0 Reserved 000000 FILE_FORMAT_GRP 15 1 File format group 0 W(1) COPY 14 1 Copy flag 0 W(1) PERM_WRITE_PROTECT 13 1 Permanent write protection 0 W(1) TMP_WRITE_PROTECT 12 1 Temporary write protection 0 W FILE_FORMAT 11 2 File format 00 W(1) TMP_WRITE_PROTECT 12 1 Temporary write protection 0 W FILE_FORMAT 11 2 File format 00 W(1) CCCC 7 7 Checksum of CSD contents xxxxxxxx W	C_SIZE_MULT	49	3	Device size multiplier	110*)
WP_GRP_SIZE387Write protect group size0000001*)WP_GRP_ENABLE311Write protect group enable0	ERASE_BLK_EN	46	1	Erase single block enable	1
WP_GRP_ENABLE 31 1 Write protect group enable 0 R2W_FACTOR 28 3 Write speed factor 100 WRITE_BL_LEN 25 4 Write data block length 1001*) WRITE_BL_PARTIAL 21 1 Partial blocks for write allowed 0	SECTOR_SIZE	45	7	Erase sector size	1111111
R2W_FACTOR 28 3 Write speed factor 100 WRITE_BL_LEN 25 4 Write data block length 1001*) WRITE_BL_PARTIAL 21 1 Partial blocks for write allowed 0	WP_GRP_SIZE	38	7	Write protect group size	000001*)
R2W_FACTOR 28 3 Write speed factor 100 WRITE_BL_LEN 25 4 Write data block length 1001*) WRITE_BL_PARTIAL 21 1 Partial blocks for write allowed 0	WP_GRP_ENABLE	31	1	Write protect group enable	0
WRITE_BL_LEN 25 4 Write data block length 1001*) WRITE_BL_PARTIAL 21 1 Partial blocks for write allowed 0	_	30	2		00
WRITE_BL_PARTIAL 21 1 Partial blocks for write allowed 0	R ₂ W_FACTOR	28	3	Write speed factor	100
— 20 5 Reserved 00000 FILE_FORMAT_GRP 15 1 File format group 0 W(1) COPY 14 1 Copy flag 0 W(1) PERM_WRITE_PROTECT 13 1 Permanent write protection 0 W(1) IMP_WRITE_PROTECT 12 1 Temporary write protection 0 W FILE_FORMAT 11 2 File format 00 W(1) — 9 2 Reserved 00 W CRC 7 7 Checksum of CSD contents xxxxxxxxx W	WRITE_BL_LEN	25	4		1001*)
FILE_FORMAT_GRP 15 1 File format group o W(1) COPY 14 1 Copy flag o W(1) PERM_WRITE_PROTECT 13 1 Permanent write protection o W(1) IMP_WRITE_PROTECT 12 1 Temporary write protection o W FILE_FORMAT 11 2 File format oo W(1) - 9 2 Reserved oo W CRC 7 7 Checksum of CSD contents xxxxxxxxx W	WRITE_BL_PARTIAL	21	1	Partial blocks for write allowed	0
COPY 14 1 Copy flag 0 W(1) PERM_WRITE_PROTECT 13 1 Permanent write protection 0 W(1) IMP_WRITE_PROTECT 12 1 Temporary write protection 0 W FILE_FORMAT 11 2 File format 00 W(1) - 9 2 Reserved 00 W CRC 7 7 Checksum of CSD contents xxxxxxxx W	_	20	5	Reserved	00000
COPY 14 1 Copy flag 0 W(1) PERM_WRITE_PROTECT 13 1 Permanent write protection 0 W(1) IMP_WRITE_PROTECT 12 1 Temporary write protection 0 W FILE_FORMAT 11 2 File format 00 W(1) 9 2 Reserved 00 W CRC 7 7 Checksum of CSD contents xxxxxxxxx W	FILE_FORMAT_GRP	15	1	File format group	o W(1)
IMP_WRITE_PROTECT 12 1 Temporary write protection 0 W FILE_FORMAT 11 2 File format 00 W(1) - 9 2 Reserved 00 W CRC 7 7 Checksum of CSD contents xxxxxxxxx W	COPY	14	1		o W(1)
FILE_FORMAT 11 2 File format 00 W(1) - 9 2 Reserved 00 W CRC 7 7 Checksum of CSD contents xxxxxxxxx W	PERM_WRITE_PROTECT	13	1	Permanent write protection	o W(1)
FILE_FORMAT 11 2 File format 00 W(1) - 9 2 Reserved 00 W CRC 7 7 Checksum of CSD contents xxxxxxxxx W	TMP_WRITE_PROTECT	12	1		o W
CRC 7 7 Checksum of CSD contents xxxxxxxx W	FILE_FORMAT	11	2	File format	00 W(1)
		9	2	Reserved	oo W
0	CRC	7	7	Checksum of CSD contents	xxxxxxx W
	_	0	1	Always=1	1

^{*)} Drive Size and block sizes vary with card capacity

memory capacity = BLOCKNR * BLOCK_LEN

Where

BLOCKNR = (C_SIZE+1) * MULT

MULT = 2^{C_SIZE_MULT+2} (C_SIZE_MULT < 8) BLOCK_LEN = 2^{READ_BL_LEN}, (READ_BL_LEN < 12)

value can be changed with CMD27 (PROGRAM_CSD)

W(1) value can be changed **ONCE** with CMD27 (PROGRAM_CSD)



Table 24: SCR register

ingle =4. part tellipte:			
Field	Bit Width	typ Value	
SCR_STRUCTURE	4	0000	
SD_SPEC	4	0010	
DATA_STAT_AFTER_ERASE	1	1	
SD_SECURITY	3	011	
SD_BUS_WIDTHS	4	0101	
Reserved	16	0	
Reserved	32	0	•

Table 25: RCA register

Field	Bit Width	typ Value
RCA	16	0x0000*)

^{*)} After Initialization the card can change the RCA register.



8 Card Lifetime Information Data

Swissbit S-200/S-220 cards provide various lifetime monitoring information in the "reserved for manufacturer" field of the SD Status register. This data can be read out using ACMD13 (SD_STATUS) on host systems with a native SD-Interface (e.g. embedded systems, SD or SPI interface or PCI/SD-reader).

We recommend assessing the expected/guaranteed life time of Flash based devices to make sure the product life time fulfills your expectations. The real application workload should be tested in a test installation or simulation for best accuracy.

In general, calculations based on application behavior statistics are not possible as the influence of the operating systems (with the caches) and the file system have a big influence on the data actually written on the device.

This product does report the real erase cycles that the NAND Flash blocks have seen. Based on the average erase count and it's ascend in the target system, it is possible to quite simply calculate the expected life time of the product.

Bad and spare block counts can't be used for linear life time calculations. In the beginning of the device life time, only very few blocks will be needed to be replaced. Generally if a device reaches the end of the lifetime, more bad blocks will occur.

The SD Status is defined by the SD Standard and contains several status bits as well as a field for manufacturer specific data. The overall size of the SD Status is one data block of 512 bits divided into 312 reserved for manufacturer bits used for the Swissbit lifetime information and 200 bits for other purposes, defined by the SDA.

The content of the SD Status register is transmitted to the Host over the DAT bus along with a 16-bit CRC. The SD Status is sent to the host over the DAT bus as a response to ACMD13 (CMD55 followed with CMD13). ACMD13 can be sent to a card only in "tran_state" (card is selected).

Please note that it is not possible so set up the necessary command (ACMD13) through a common USB/SD-card reader/bridge. In contrast to that, a lot of embedded systems and PCIe card readers support the command.

Swissbit provides a demo code written in C for Linux systems on demand.

Table 26: SD Status and Lifetime Information sector decoding

Bits	Description (All values MSb first)
r . 1	
[511:312]	SD Status field as defined in the Physical Layer Specification Version 2.00
[]	(Not relevant for Card Lifetime Info)
[311:304]	Data structure version identifier ("o" for S-200/S-220 cards)
[303:288]	Number of initial defect blocks
[287:272]	Number of initial spare blocks, 1st flash CE (across channels) big Endian
[271:256]	Number of initial spare blocks, 2 nd flash CE (across channels) big Endian
[255:248]	Percentage of remaining spare blocks, first flash CE (across channels)
[247:240]	Percentage of remaining spare blocks, second flash CE (across channels)
[239:224]	(Reserved)
[223:192]	(Reserved)
[191:176]	Lowest wear level class (WL)
[175:160]	Highest wear level class (WH)
[159:144]	Wear level threshold (T)
[143:96]	Total number of block erases
[95:80]	Number of flash blocks
[79:64]	Maximum flash block erase count target, in wear level class units
[63:32]	Power on count
[31:24]	(Reserved)
[23:16]	(Reserved)
[15:8]	(Reserved)
[7:0]	(Reserved)



The lowest wear level class (WL) and highest wear level class (WH) fields give the range of wear level classes currently in use. The wear level threshold (T) gives the size of a wear level class, minus 1, in units of flash memory block erases. Thus, the number of block erases that the flash blocks have seen is between WL*(T+1) and WH*(T+1)-1.



9 RoHS and WEEE update from Swissbit

Dear Valued Customer,

We at Swissbit place great value on the environment and thus pay close attention to the diverse aspects of manufacturing environmentally and health friendly products. The European Parliament and the Council of the European Union have published two Directives defining a European standard for environmental protection. This states that CompactFlash Cards must comply with both Directives in order for them to be sold on the European market:

- RoHS Restriction of Hazardous Substances
- WEEE Waste Electrical and Electronic Equipment

Swissbit would like to take this opportunity to inform our customers about the measures we have implemented to adapt all our products to the European norms.

What is the WEEE Directive (2012/19/EU)?

The Directive covers the following points:

- Prevention of WEEE
- Recovery, recycling and other measures leading to a minimization of wastage of electronic and electrical equipment
- Improvement in the quality of environmental performance of all operators involved in the EEE life cycle, as well as measures to incorporate those involved at the EEE waste disposal points

What are the key elements?

The WEEE Directive covers the following responsibilities on the part of producers:

Producers must draft a disposal or recovery scheme to dispose of EEE correctly.

Producers must be registered as producers in the country in which they distribute the goods. They must also supply and publish information about the EEE categories.

Producers are obliged to finance the collection, treatment and disposal of WEEE.

Inclusion of WEEE logos on devices

In reference to the Directive, the WEEE logo must be printed directly on all devices that have sufficient space. «In exceptional cases where this is necessary because of the size of the product, the symbol of the WEEE Directive shall be printed on the packaging, on the instructions of use and on the warranty» (WEEE Directive 2012/19/EU)

When does the WEEE Directive take effect?

The Directive came into effect internationally on 13 August, 2005.

What is RoHS (2011/65/EU)?

The goals of the Directive are to:

- Place less of a burden on human health and to protect the environment by restricting the use of hazardous substances in new electrical and electronic devices
- To support the WEEE Directive (see above)

RoHS enforces the restriction of the following 6 hazardous substances in electronic and electrical devices:

- Lead (Pb) no more than 0.1% by weight in homogeneous materials
- Mercury (Hg) no more than 0.1% by weight in homogeneous materials
- Cadmium (Cd) no more than 0.01% by weight in homogeneous materials
- Chromium (Cr6+) no more than 0.1% by weight in homogeneous materials
- PBB, PBDE no more than 0.1% by weight in homogeneous materials



Swissbit is obliged to minimize the hazardous substances in the products.

According to part of the Directive, manufacturers are obliged to make a self-declaration for all devices with RoHS. Swissbit carried out intensive tests to comply with the self-declaration. We have also already taken steps to have the analyses of the individual components guaranteed by third-party companies.

Swissbit carried out the following steps during the year with the goal of offering our customers products that are fully compliant with the RoHS Directive.

- Preparing all far-reaching directives, logistical enhancements and alternatives regarding the full understanding and introduction of the RoHS Directive's standards
- Checking the components and raw materials:
 - Replacing non-RoHS-compliant components and raw materials in the supply chain
 - Cooperating closely with suppliers regarding the certification of all components and raw materials used by Swissbit
- Modifying the manufacturing processes and procedures
 - Successfully adapting and optimizing the new management-free integration process in the supply chain
 - Updating existing production procedures and introducing the new procedures to support the integration process and the sorting of materials
- Carrying out the quality process
 - Performing detailed function and safety tests to ensure the continuous high quality of the Swissbit product line

When does the RoHS Directive take effect?

As of June 08, 2011 only new electrical and electronic devices with approved quantities of RoHS will be put on the market.

When will Swissbit be offering RoHS-approved products?

Swissbit's RoHS-approved products are available now. Please contact your Swissbit contact person to find out more about exchanging your existing products for RoHS-compliant devices.

For your attention

We understand that packaging and accessories are not EEE material and are therefore not subject to the WEEE or RoHS Directives.

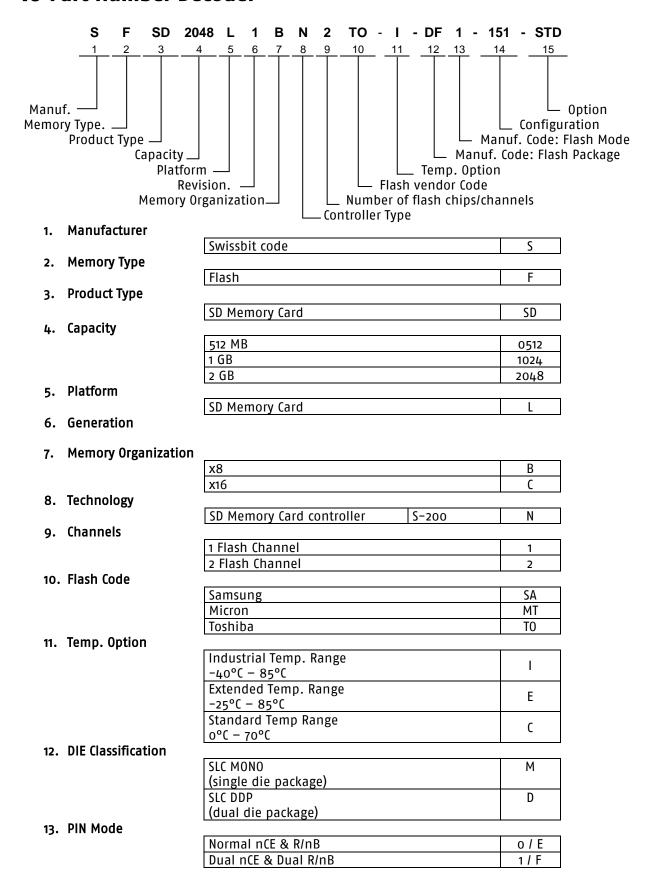
Contact details: Swissbit AG Industriestrasse 4 CH 9552 Bronschhofen

Tel: +41 71 913 03 03 - Fax: +41 71 913 03 15

E-mail: industrial@swissbit.com - Website: www.swissbit.com



10 Part Number Decoder





14. Configuration XYZ

X→ Configuration

Configuration	Х
default	1

Y → FW Revision

FW Revision	Υ
Revision 1	1
Revision 2	2
Revision 3	3
Revision 4	4
Revision 5	5
Revision 6	6

$Z \rightarrow optional$

Optional	Z
optional	1

15. Option

Swissbit / Standard STD



11 Swissbit Label specification

11.1 Front side label



512MB SD Memory Card



1GB SD Memory Card



2GB SD Memory Card

11.2 Back side lasering



SWISSBIT
SFSD1024L1BN2
T0-I-ME-151-STD
1012-60012345
Made in Germany
CE WEEE

Partnumber Date-Lot/Serial

Example of the back side laser marking



12 Revision History

Table 27: Document Revision History

Date	Revision	Revision Details
23-Jul-2008	1.00	Initial release
10-Dec-2008	1.02	S-200/S-210 series added, current values actualized
		better real speed values in CSD TAAC and R2W_Factor
		other CSD register corrections, document structure, new generation added
06-Mar-2009	1.03	1GB capacity corrected, FW update
04-Dec-2009	1.10	latest FW update, CMD class 7 (Lock card) added for new firmware, write CSD specified,
		disk size for the FW version 3 by the 1GB card adapted
28-Jul-2010	1.11	Correct High-Speed mode timing diagram, part numbers
30-Mar-2011	1.20	Samsung-NAND-Flash Versions are End of Life, and removed from Datasheet.
		New 512MB – 2GB Toshiba-NAND-Flash Versions added, Part number Codes updated,
		speed and current values updated
17-Feb-2012	1.21	Performance values updated, label and lasering update
27-Apr-2012	1.30	SDA Correction, CI update
18-June-2012	1.31	FW-Rev. 6 added
11-December-2012	1.40	New CE Declaration, new picture back side lasering
17-February-2014	1.50	DC and AC characteristics updated, CE Declaration removed
12-February-2015	1.51	Added chapter 8 "Card Lifetime Information Data"

Disclaimer:

No part of this document may be copied or reproduced in any form or by any means, or transferred to any third party, without the prior written consent of an authorized representative of Swissbit AG ("SWISSBIT"). The information in this document is subject to change without notice. SWISSBIT assumes no responsibility for any errors or omissions that may appear in this document, and disclaims responsibility for any consequences resulting from the use of the information set forth herein. SWISSBIT makes no commitments to update or to keep current information contained in this document. The products listed in this document are not suitable for use in applications such as, but not limited to, aircraft control systems, aerospace equipment, submarine cables, nuclear reactor control systems and life support systems. Moreover, SWISSBIT does not recommend or approve the use of any of its products in life support devices or systems or in any application where failure could result in injury or death. If a customer wishes to use SWISSBIT products in applications not intended by SWISSBIT, said customer must contact an authorized SWISSBIT representative to determine SWISSBIT willingness to support a given application. The information set forth in this document does not convey any license under the copyrights, patent rights, trademarks or other intellectual property rights claimed and owned by SWISSBIT. The information set forth in this document is considered to be "Proprietary" and "Confidential" property owned by SWISSBIT.

ALL PRODUCTS SOLD BY SWISSBIT ARE COVERED BY THE PROVISIONS APPEARING IN SWISSBIT'S TERMS AND CONDITIONS OF SALE ONLY, INCLUDING THE LIMITATIONS OF LIABILITY, WARRANTY AND INFRINGEMENT PROVISIONS. SWISSBIT MAKES NO WARRANTIES OF ANY KIND, EXPRESS, STATUTORY, IMPLIED OR OTHERWISE, REGARDING INFORMATION SET FORTH HEREIN OR REGARDING THE FREEDOM OF THE DESCRIBED PRODUCTS FROM INTELLECTUAL PROPERTY INFRINGEMENT, AND EXPRESSLY DISCLAIMS ANY SUCH WARRANTIES INCLUDING WITHOUT LIMITATION ANY EXPRESS, STATUTORY OR IMPLIED WARRANTIES OF MERCHANTABILITY OR FITNESS FOR A PARTICULAR PURPOSE.

©2015 SWISSBIT AG All rights reserved.



Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию.

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России, а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

Наши контакты:

Телефон: +7 812 627 14 35

Электронная почта: sales@st-electron.ru

Адрес: 198099, Санкт-Петербург,

Промышленная ул, дом № 19, литера Н,

помещение 100-Н Офис 331